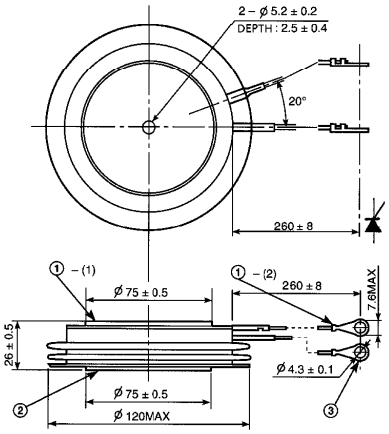
TOSHIBA THYRISTOR SILICON DIFFUSED TYPE

SF2500EX23

HIGH POWER CONTROL APPLICATIONS

- Repetitive Peak Off-State Voltage : V_{DRM} } = 2500V
  Repetitive Peak Reverse Voltage : V_{RRM} }
- Average On-State Current : $I_{T(AV)}$ = 2500A
- Turn-Off Time : t_q = 400 μs (Max.)
- Critical Rate of Rise of On-State Current : di / dt = 250A / μs
- Critical Rate of Rise of Off-State Voltage : dv / dt = 1500V / μs
- Flat Package

Unit in mm



1- (1) CATHODE
1- (2) CATHODE (BLACK)
2. ANODE
3. GATE (WHITE)

JEDEC	—
EIAJ	—
TOSHIBA	13-120J1A

Weight : 1350g

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage	V_{DRM} V_{RRM}	2500	V
Non-Repetitive Peak Reverse Voltage (Non-Repetitive < 5ms, T_j = 0~125°C)	V_{RSM}	2750	V
R.M.S On-State Current	$I_{T(RMS)}$	3925	A
Average On-State Current	$I_{T(AV)}$	2500	A
Peak One Cycle Surge On-State Current (Non-Repetitive)	I_{TSM}	50000 (50Hz)	A
		55000 (60Hz)	
I^2t Limit Value	I^2t	1.25×10^7	A^2s
Critical Rate of Rise of On-State Current (Note)	di / dt	250	A / μs
Peak Gate Power Dissipation	P_{GM}	30	W
Average Gate Power Dissipation	$P_{G(AV)}$	4	W
Peak Forward Gate Current	I_{GM}	6	A
Peak Forward Gate Voltage	V_{FGM}	30	V
Peak Reverse Gate Voltage	V_{RGM}	5	V
Junction Temperature	T_j	−40~125	°C
Storage Temperature Range	T_{stg}	−40~125	°C
Mounting Force	—	39.2±3.9	kN

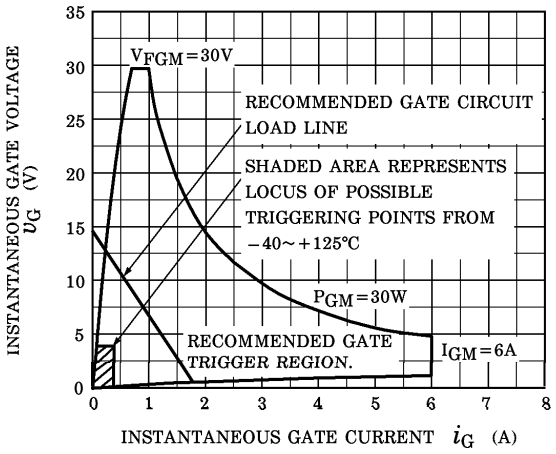
Note : V_D = 1250V, f = 50Hz, T_j = 125°C, Gate Supply (V_G = 15V, R_G = 8Ω, $t_r \leqq 1\mu s$)

961001EAA2

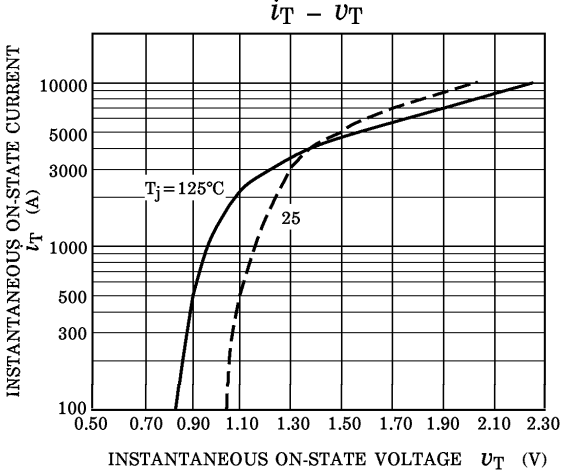
ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	MAX.	UNIT
Repetitive Peak Off-State Current and Repetitive Peak Reverse Current	I_{DRM} I_{RRM}	$V_{DRM}=V_{RRM}=2500V$, $T_j=125°C$		—	120	mA
Peak On-State Voltage	V_{TM}	$I_{TM}=8000A$, $T_j=25°C$		—	1.82	V
Gate Trigger Voltage	V_{GT}	$V_D=12V$, $R_L=6\Omega$	$T_j=-40°C$	—	4.0	V
			$T_j=25°C$	—	2.5	
Gate Trigger Current	I_{GT}		$T_j=-40°C$	—	400	mA
			$T_j=25°C$	—	250	
Gate Non-Trigger Voltage	V_{GD}	$V_D=1250V$, $T_j=125°C$		0.2	—	V
Gate Non-Trigger Current	I_{GD}			5	—	mA
Delay Time	t_d	$V_D=1250V$, $T_j=25°C$ Gate Supply ($V_G=15V$, $R_G=8\Omega$, $t_r\leqq 1\mu s$)		—	5	μs
Gate Turn-On Time	t_{gt}			—	10	μs
Turn-Off Time	t_q	$I_T=1200A$, $V_R\geqq 200V$ $dv/dt=25V/\mu s$, $T_j=115°C$ $V_{DRM}=1250V$		—	400	μs
Holding Current	I_H	$T_j=25°C$, $R_L=6\Omega$		—	300	mA
Critical Rate of Rise of Off-State Voltage	dv/dt	$V_{DRM}=1670V$, $T_j=125°C$ Gate Open Exponential Rise		1500	—	$V/\mu s$
Thermal Resistance	$R_{th\,(j\text{-}f)}$	Junction to Fin		—	0.0125	°C / W

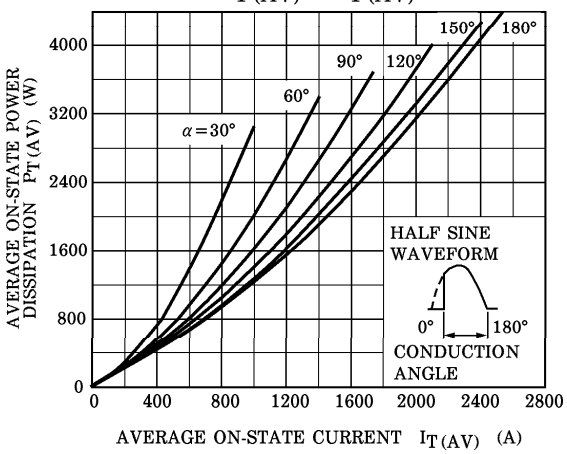
GATE TRIGGER CHARACTERISTIC



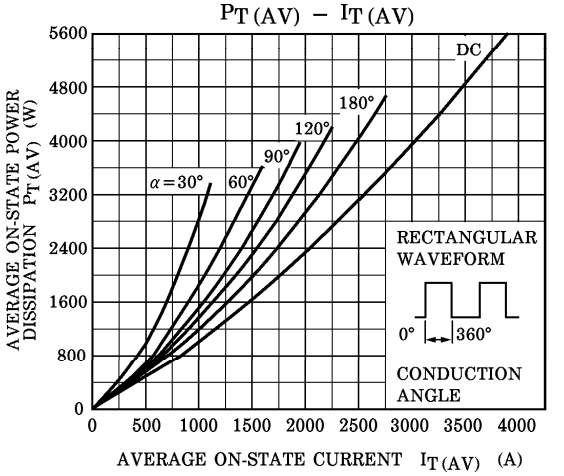
$i_T - v_T$



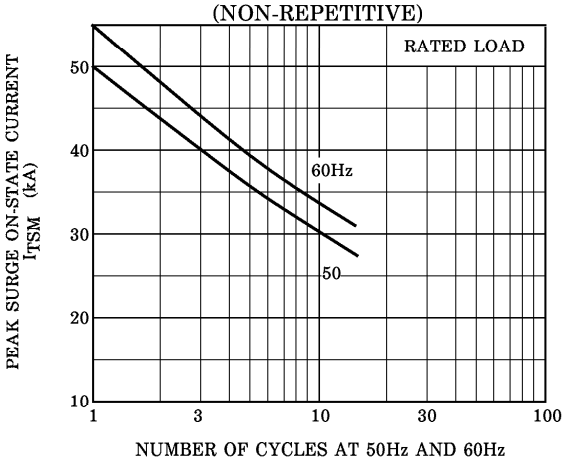
$P_{T(AV)} - I_{T(AV)}$



$P_{T(AV)} - I_{T(AV)}$



SURGE ON-STATE CURRENT (NON-REPETITIVE)



TRANSIENT THERMAL IMPEDANCE (JUNCTION TO FIN)